

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions and listings of claims in the application.

### **LISTING OF CLAIMS**

1. (Currently Amended) An electro-optic device comprising:  
a pair of substrates;  
an electro-optic material disposed between the substrates; ~~and~~  
~~means for applying an electric field to the electro-optic material;~~  
a material enclosure region in which the electro-optic material is enclosed;  
[[a]] reflection electrodes provided on one of the pair of substrates in the material enclosure region, the reflection electrodes having a multilayer structure including:  
a reflective conductive layer made of one of silver and a silver alloy; and  
a transparent conductive layer provided on the reflective conductive layer;  
and  
external wirings connected to the reflection electrodes and provided outside the material enclosure region, the external wirings having a transparent conductive layer equivalent to that of the multilayer structure;  
wherein the transparent conductive layer of the reflection electrodes has a thickness larger than that of the reflective conductive layer.
2. (Original) The electro-optic device of Claim 1, wherein the reflective conductive layer has a thickness of 80 nm to 300 nm.

3. (Original) The electro-optic device of Claim 1, further comprising an underlying insulating layer between said one of the pair of substrates and said reflective conductive layers.

4. (Currently Amended) A method for manufacturing an electro-optic device having a pair of substrates[[,]] and an electro-optic material provided between the substrates, ~~and means for applying an electric field to the electro-optic material~~, the method comprising:

a step of selectively forming reflective conductive layers made of one of silver and a silver alloy on one of the pair of substrates only in a first region to be used as a material enclosure region in which the electro-optic material is enclosed; and

a step of forming transparent conductive layers in the first region and a second region located outside the material enclosure region, the transparent conductive layers having a thickness larger than that of the reflective conductive layers.

5. (Original) The method for manufacturing an electro-optic device of Claim 4, wherein the reflective conductive layers are formed to have a thickness of 80 nm to 300 nm.

6. (Original) The method for manufacturing an electro-optic device of Claim 4, further comprising a step of forming an underlying insulating layer between said one of the pair of substrates and the reflective conductive layers.

7. (Original) An electronic apparatus comprising:  
the electro-optic device according to Claim 1; and  
control means for controlling the electro-optic device.

8. (New) The electro-optical device of Claim 1, wherein the transparent  
conductive layer is from about 30nm to about 50nm thicker than the reflective  
conductive layer.

9. (New) The method of Claim 4, wherein the transparent conductive layers  
are from about 30nm to about 50nm thicker than the reflective conductive layers.